

## AMENDMENTS TO THE ABSTRACT

### **In the Abstract:**

Please cancel the Abstract of Disclosure and substitute the following:

--       A dual damascene process is disclosed which reduces capacitance increases caused by excess and unnecessary remnants of an etching stop layer and which also improves multi-level interconnect structures by removing the etching stop layer except for a portion that surrounds the via hole. This reduces or eliminates capacitance increase and avoids erosion of underlying interlayer insulating layers during formation of an upper, wider trench. --